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Embedded microprocessors are specialized computing chips designed to perform specific tasks within an embedded system. Unlike general-purpose microprocessors found in personal computers, embedded microprocessors are tailored for dedicated functions within larger systems, offering optimized performance, efficiency, and reliability. These microprocessors are integral to the operation of countless electronic devices, providing the computational power necessary for controlling processes, handling data, and managing communications.

Applications of [Embedded - Microprocessors](#)

Embedded microprocessors are utilized across a broad spectrum of applications, making them indispensable in

Details

Product Status	Obsolete
Core Processor	PowerPC e300
Number of Cores/Bus Width	1 Core, 32-Bit
Speed	533MHz
Co-Processors/DSP	Communications; QUICC Engine, Security; SEC
RAM Controllers	DDR, DDR2
Graphics Acceleration	No
Display & Interface Controllers	-
Ethernet	10/100/1000Mbps (1)
SATA	-
USB	USB 1.x (1)
Voltage - I/O	1.8V, 2.5V, 3.3V
Operating Temperature	-40°C ~ 105°C (TA)
Security Features	Cryptography, Random Number Generator
Package / Case	740-LBGA
Supplier Device Package	740-TBGA (37.5x37.5)
Purchase URL	https://www.e-xfl.com/product-detail/nxp-semiconductors/mpc8360ecvvajdga

- DRAM chip configurations from 64 Mbits to 1 Gigabit with $\times 8/\times 16$ data ports
- Full ECC support (when the MPC8360E is configured as 2×32 -bit DDR memory controllers, both support ECC)
- Page mode support (up to 16 simultaneous open pages for DDR1, up to 32 simultaneous open pages for DDR2)
- Contiguous or discontinuous memory mapping
- Read-modify-write support
- Sleep mode support for self refresh SDRAM
- Supports auto refreshing
- Supports source clock mode
- On-the-fly power management using CKE
- Registered DIMM support
- 2.5-V SSTL2 compatible I/O for DDR1, 1.8-V SSTL2 compatible I/O for DDR2
- External driver impedance calibration
- On-die termination (ODT)
- PCI interface
 - PCI Specification Revision 2.3 compatible
 - Data bus widths:
 - Single 32-bit data PCI interface that operates at up to 66 MHz
 - PCI 3.3-V compatible (not 5-V compatible)
 - PCI host bridge capabilities on both interfaces
 - PCI agent mode supported on PCI interface
 - Support for PCI-to-memory and memory-to-PCI streaming
 - Memory prefetching of PCI read accesses and support for delayed read transactions
 - Support for posting of processor-to-PCI and PCI-to-memory writes
 - On-chip arbitration, supporting five masters on PCI
 - Support for accesses to all PCI address spaces
 - Parity support
 - Selectable hardware-enforced coherency
 - Address translation units for address mapping between host and peripheral
 - Dual address cycle supported when the device is the target
 - Internal configuration registers accessible from PCI
- Local bus controller (LBC)
 - Multiplexed 32-bit address and data operating at up to 133 MHz
 - Eight chip selects support eight external slaves
 - Up to eight-beat burst transfers
 - 32-, 16-, and 8-bit port sizes are controlled by an on-chip memory controller
 - Three protocol engines available on a per chip select basis:
 - General-purpose chip select machine (GPCM)
 - Three user programmable machines (UPMs)
 - Dedicated single data rate SDRAM controller
 - Parity support
 - Default boot ROM chip select with configurable bus width (8-, 16-, or 32-bit)
- Programmable interrupt controller (PIC)
 - Functional and programming compatibility with the MPC8260 interrupt controller
 - Support for 8 external and 35 internal discrete interrupt sources
 - Support for one external (optional) and seven internal machine checkstop interrupt sources

This figure shows the undershoot and overshoot voltage of the PCI interface of the device for the 3.3-V signals, respectively.

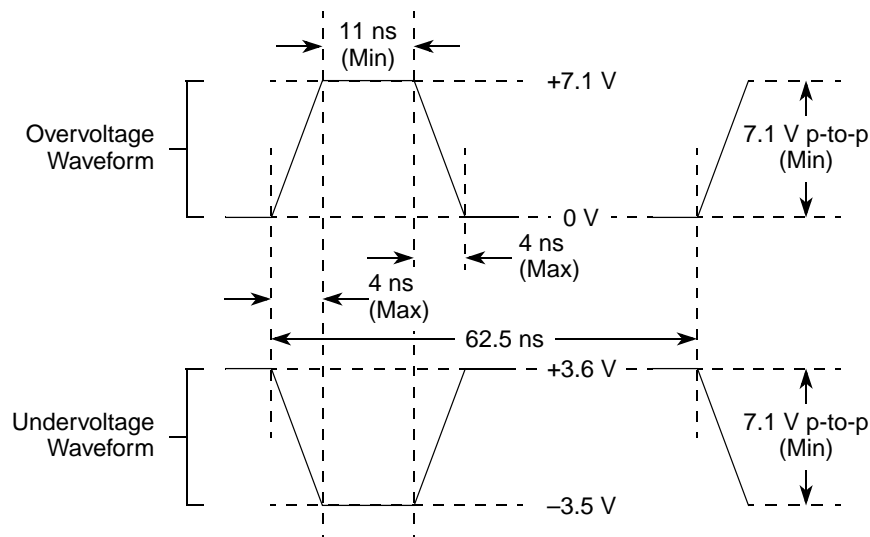


Figure 4. Maximum AC Waveforms on PCI interface for 3.3-V Signaling

2.1.3 Output Driver Characteristics

This table provides information on the characteristics of the output driver strengths. The values are preliminary estimates.

Table 3. Output Drive Capability

Driver Type	Output Impedance (Ω)	Supply Voltage
Local bus interface utilities signals	42	$OV_{DD} = 3.3\text{ V}$
PCI signals	25	
PCI output clocks (including PCI_SYNC_OUT)	42	
DDR signal	20 36 (half-strength mode) ¹	$GV_{DD} = 2.5\text{ V}$
DDR2 signal	18 36 (half-strength mode) ¹	$GV_{DD} = 1.8\text{ V}$
10/100/1000 Ethernet signals	42	$LV_{DD} = 2.5/3.3\text{ V}$
DUART, system control, I ² C, SPI, JTAG	42	$OV_{DD} = 3.3\text{ V}$
GPIO signals	42	$OV_{DD} = 3.3\text{ V}$ $LV_{DD} = 2.5/3.3\text{ V}$

Note:

1. DDR output impedance values for half strength mode are verified by design and not tested.

2.2 Power Sequencing

This section details the power sequencing considerations for the MPC8360E/58E.

This table shows the estimated typical I/O power dissipation for the device.

Table 6. Estimated Typical I/O Power Dissipation

Interface	Parameter	GV _{DD} (1.8 V)	GV _{DD} (2.5 V)	OV _{DD} (3.3 V)	LV _{DD} (3.3 V)	LV _{DD} (2.5 V)	Unit	Comments
DDR I/O 65% utilization R _s = 20 Ω R _t = 50 Ω 2 pairs of clocks	200 MHz, 1 × 32 bits	0.3	0.46	—	—	—	W	—
	200 MHz, 1 × 64 bits	0.4	0.58	—	—	—	W	—
	200 MHz, 2 × 32 bits	0.6	0.92	—	—	—	W	—
	266 MHz, 1 × 32 bits	0.35	0.56	—	—	—	W	—
	266 MHz, 1 × 64 bits	0.46	0.7	—	—	—	W	—
	266 MHz, 2 × 32 bits	0.7	1.11	—	—	—	W	—
	333 MHz, 1 × 32 bits	0.4	0.65	—	—	—	W	—
	333 MHz, 1 × 64 bits	0.53	0.82	—	—	—	W	—
	333 MHz, 2 × 32 bits	0.81	1.3	—	—	—	W	—
Local Bus I/O Load = 25 pF 3 pairs of clocks	133 MHz, 32 bits	—	—	0.22	—	—	W	—
	83 MHz, 32 bits	—	—	0.14	—	—	W	—
	66 MHz, 32 bits	—	—	0.12	—	—	W	—
	50 MHz, 32 bits	—	—	0.09	—	—	W	—
PCI I/O Load = 30 pF	33 MHz, 32 bits	—	—	0.05	—	—	W	—
	66 MHz, 32 bits	—	—	0.07	—	—	W	—
10/100/1000 Ethernet I/O Load = 20 pF	MII or RMII	—	—	—	0.01	—	W	Multiply by number of interfaces used.
	GMII or TBI	—	—	—	0.04	—	W	
	RGMII or RTBI	—	—	—	—	0.04	W	
Other I/O	—	—	—	0.1	—	—	W	—

4 Clock Input Timing

This section provides the clock input DC and AC electrical characteristics for the MPC8360E/58E.

NOTE

The rise/fall time on QUICC Engine block input pins should not exceed 5 ns. This should be enforced especially on clock signals. Rise time refers to signal transitions from 10% to 90% of V_{DD}; fall time refers to transitions from 90% to 10% of V_{DD}.

6.1 DDR and DDR2 SDRAM DC Electrical Characteristics

This table provides the recommended operating conditions for the DDR2 SDRAM component(s) of the device when $GV_{DD}(\text{typ}) = 1.8 \text{ V}$.

Table 14. DDR2 SDRAM DC Electrical Characteristics for $GV_{DD}(\text{typ}) = 1.8 \text{ V}$

Parameter/Condition	Symbol	Min	Max	Unit	Notes
I/O supply voltage	GV_{DD}	1.71	1.89	V	1
I/O reference voltage	MV_{REF}	$0.49 \times GV_{DD}$	$0.51 \times GV_{DD}$	V	2
I/O termination voltage	V_{TT}	$MV_{REF} - 0.04$	$MV_{REF} + 0.04$	V	3
Input high voltage	V_{IH}	$MV_{REF} + 0.125$	$GV_{DD} + 0.3$	V	—
Input low voltage	V_{IL}	-0.3	$MV_{REF} - 0.125$	V	—
Output leakage current	I_{OZ}	—	± 10	μA	4
Output high current ($V_{OUT} = 1.420 \text{ V}$)	I_{OH}	-13.4	—	mA	—
Output low current ($V_{OUT} = 0.280 \text{ V}$)	I_{OL}	13.4	—	mA	—
MV_{REF} input leakage current	I_{VREF}	—	± 10	μA	—
Input current ($0 \text{ V} \leq V_{IN} \leq OV_{DD}$)	I_{IN}	—	± 10	μA	—

Notes:

- GV_{DD} is expected to be within 50 mV of the DRAM GV_{DD} at all times.
- MV_{REF} is expected to equal $0.5 \times GV_{DD}$, and to track GV_{DD} DC variations as measured at the receiver. Peak-to-peak noise on MV_{REF} cannot exceed $\pm 2\%$ of the DC value.
- V_{TT} is not applied directly to the device. It is the supply to which far end signal termination is made and is expected to equal MV_{REF} . This rail should track variations in the DC level of MV_{REF} .
- Output leakage is measured with all outputs disabled, $0 \text{ V} \leq V_{OUT} \leq GV_{DD}$.

This table provides the DDR2 capacitance when $GV_{DD}(\text{typ}) = 1.8 \text{ V}$.

Table 15. DDR2 SDRAM Capacitance for $GV_{DD}(\text{typ})=1.8 \text{ V}$

Parameter/Condition	Symbol	Min	Max	Unit	Notes
Input/output capacitance: DQ, DQS, \overline{DQS}	C_{IO}	6	8	pF	1
Delta input/output capacitance: DQ, DQS, \overline{DQS}	C_{DIO}	—	0.5	pF	1

Note:

- This parameter is sampled. $GV_{DD} = 1.8 \text{ V} \pm 0.090 \text{ V}$, $f = 1 \text{ MHz}$, $T_A = 25^\circ\text{C}$, $V_{OUT} = GV_{DD}/2$, V_{OUT} (peak-to-peak) = 0.2 V.

This table provides the recommended operating conditions for the DDR SDRAM component(s) of the device when $GV_{DD}(\text{typ}) = 2.5 \text{ V}$.

Table 16. DDR SDRAM DC Electrical Characteristics for $GV_{DD}(\text{typ}) = 2.5 \text{ V}$

Parameter/Condition	Symbol	Min	Max	Unit	Notes
I/O supply voltage	GV_{DD}	2.375	2.625	V	1
I/O reference voltage	MV_{REF}	$0.49 \times GV_{DD}$	$0.51 \times GV_{DD}$	V	2
I/O termination voltage	V_{TT}	$MV_{REF} - 0.04$	$MV_{REF} + 0.04$	V	3

This table provides the input AC timing specifications for the DDR SDRAM interface when $GV_{DD}(typ) = 2.5\text{ V}$.

Table 19. DDR SDRAM Input AC Timing Specifications

At recommended operating conditions with GV_{DD} of $2.5\text{ V} \pm 5\%$.

Parameter	Symbol	Min	Max	Unit	Notes
AC input low voltage	V_{IL}	—	$MV_{REF} - 0.31$	V	—
AC input high voltage	V_{IH}	$MV_{REF} + 0.31$	—	V	—

Table 20. DDR and DDR2 SDRAM Input AC Timing Specifications Mode

At recommended operating conditions with GV_{DD} of $(1.8\text{ or }2.5\text{ V}) \pm 5\%$.

Parameter	Symbol	Min	Max	Unit	Notes
MDQS—MDQ/MECC input skew per byte 333 MHz 266 MHz 200 MHz	t_{DISKEW}	−750 −1125 −1250	750 1125 1250	ps	1, 2

Notes:

1. AC timing values are based on the DDR data rate, which is twice the DDR memory bus frequency.
2. Maximum possible skew between a data strobe ($MDQS[n]$) and any corresponding bit of data ($MDQ[8n + \{0...7\}]$ if $0 \leq n \leq 7$) or ECC ($MECC[\{0...7\}]$ if $n = 8$).

This figure shows the input timing diagram for the DDR controller.

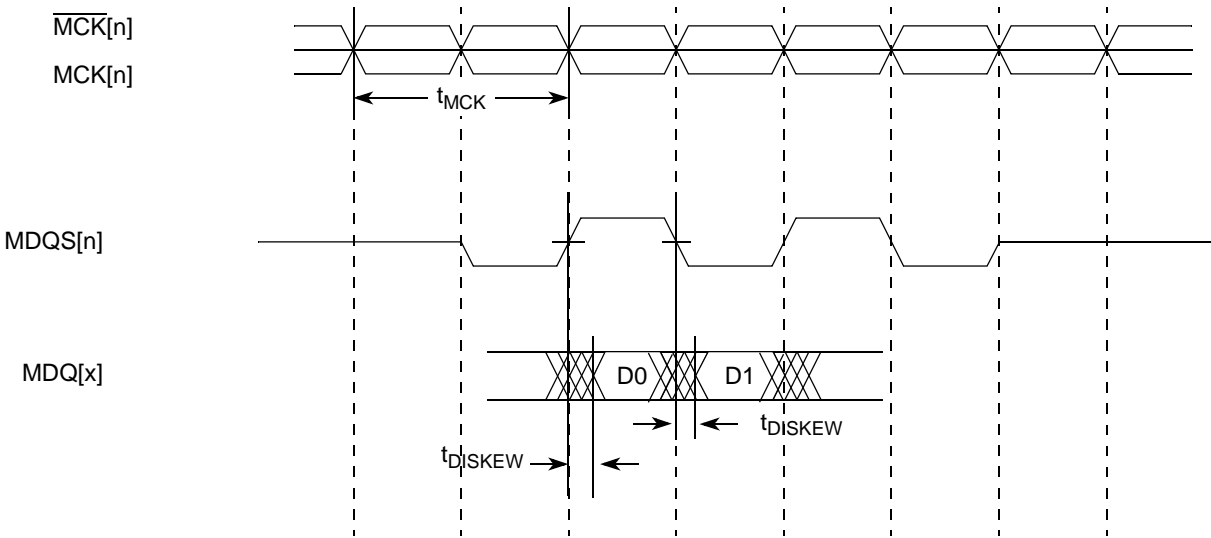


Figure 6. DDR Input Timing Diagram

6.2.2 DDR and DDR2 SDRAM Output AC Timing Specifications

Table 21 and Table 22 provide the output AC timing specifications and measurement conditions for the DDR and DDR2 SDRAM interface.

Table 21. DDR and DDR2 SDRAM Output AC Timing Specifications for Source Synchronous Mode

At recommended operating conditions with GV_{DD} of (1.8 V or 2.5 V) \pm 5%.

Parameter ⁸	Symbol ¹	Min	Max	Unit	Notes
MCK[n] cycle time, (MCK[n]/ $\overline{MCK[n]}$ crossing)	t_{MCK}	6	10	ns	2
Skew between any MCK to ADDR/CMD 333 MHz 266 MHz 200 MHz	t_{AOSKEW}	-1.0 -1.1 -1.2	0.2 0.3 0.4	ns	3
ADDR/CMD output setup with respect to MCK 333 MHz 266 MHz 200 MHz	t_{DDKHAS}	2.1 2.8 3.5	—	ns	4
ADDR/CMD output hold with respect to MCK 333 MHz 266 MHz—DDR1 266 MHz—DDR2 200 MHz	t_{DDKHAX}	2.0 2.7 2.8 3.5	—	ns	4
$\overline{MCS}(n)$ output setup with respect to MCK 333 MHz 266 MHz 200 MHz	t_{DDKHCS}	2.1 2.8 3.5	—	ns	4
$\overline{MCS}(n)$ output hold with respect to MCK 333 MHz 266 MHz 200 MHz	$t_{DDKHCSX}$	2.0 2.7 3.5	—	ns	4
MCK to MDQS	t_{DDKMH}	-0.8	0.7	ns	5, 9
MDQ/MECC/MDM output setup with respect to MDQS 333 MHz 266 MHz 200 MHz	$t_{DDKHDS},$ t_{DDKLDS}	0.7 1.0 1.2	—	ns	6
MDQ/MECC/MDM output hold with respect to MDQS 333 MHz 266 MHz 200 MHz	$t_{DDKHDX},$ t_{DDKLDX}	0.7 1.0 1.2	—	ns	6
MDQS preamble start	t_{DDKHMP}	$-0.5 \times t_{MCK} - 0.6$	$-0.5 \times t_{MCK} + 0.6$	ns	7

This figure provides the AC test load for the DDR bus.

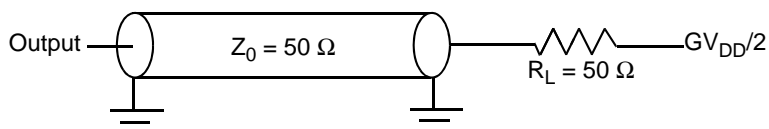


Figure 8. DDR AC Test Load

Table 22. DDR and DDR2 SDRAM Measurement Conditions

Symbol	DDR	DDR2	Unit	Notes
V_{TH}	$MV_{REF} \pm 0.31\text{ V}$	$MV_{REF} \pm 0.25\text{ V}$	V	1
V_{OUT}	$0.5 \times GV_{DD}$	$0.5 \times GV_{DD}$	V	2

Notes:

1. Data input threshold measurement point.
2. Data output measurement point.

This figure shows the DDR SDRAM output timing diagram for source synchronous mode.

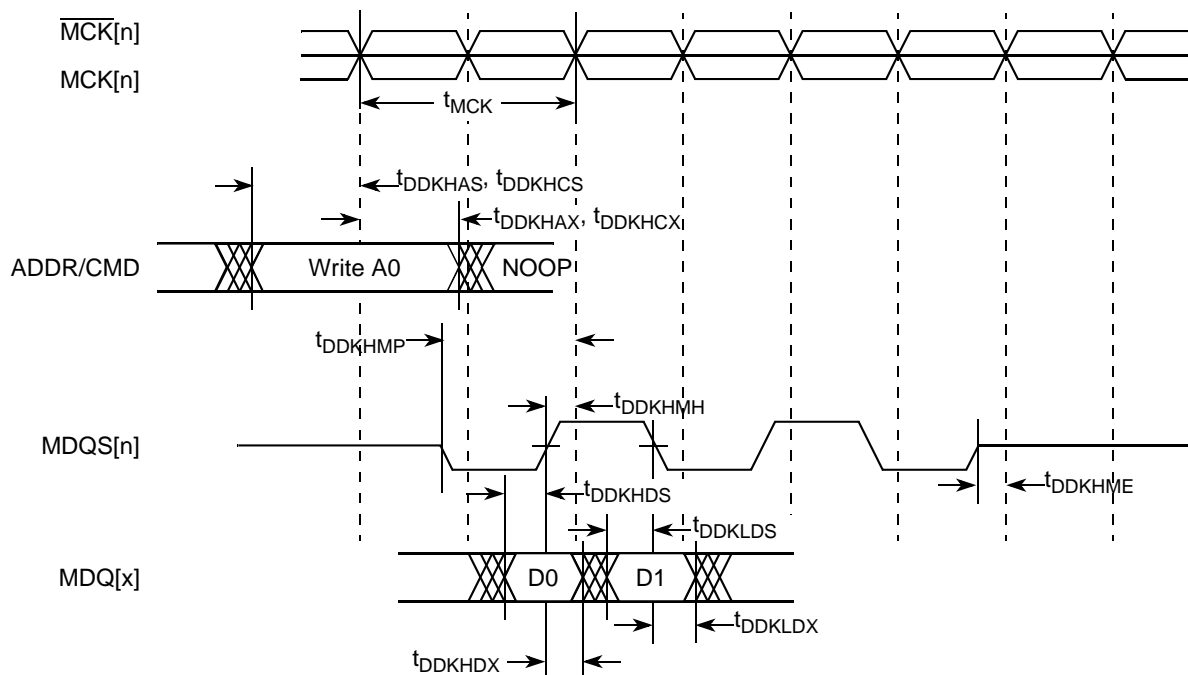


Figure 9. DDR SDRAM Output Timing Diagram for Source Synchronous Mode

8.2.1.1 GMII Transmit AC Timing Specifications

This table provides the GMII transmit AC timing specifications.

Table 27. GMII Transmit AC Timing Specifications

At recommended operating conditions with LV_{DD}/OV_{DD} of $3.3\text{ V} \pm 10\%$.

Parameter/Condition	Symbol ¹	Min	Typ	Max	Unit	Notes
GTX_CLK clock period	t_{GTX}	—	8.0	—	ns	—
GTX_CLK duty cycle	t_{GTXH}/t_{GTX}	40	—	60	%	—
GTX_CLK to GMII data TXD[7:0], TX_ER, TX_EN delay	t_{GTKHDX} t_{GTKHDV}	0.5 —	—	— 5.0	ns	3
GTX_CLK clock rise time, (20% to 80%)	t_{GTXR}	—	—	1.0	ns	—
GTX_CLK clock fall time, (80% to 20%)	t_{GTXF}	—	—	1.0	ns	—
GTX_CLK125 clock period	t_{G125}	—	8.0	—	ns	2
GTX_CLK125 reference clock duty cycle measured at $LV_{DD}/2$	t_{G125H}/t_{G125}	45	—	55	%	2

Notes:

- The symbols used for timing specifications follow the pattern $t_{(\text{first two letters of functional block})(\text{signal})(\text{state})(\text{reference})(\text{state})}$ for inputs and $t_{(\text{first two letters of functional block})(\text{reference})(\text{state})(\text{signal})(\text{state})}$ for outputs. For example, t_{GTKHDV} symbolizes GMII transmit timing (GT) with respect to the t_{GTX} clock reference (K) going to the high state (H) relative to the time date input signals (D) reaching the valid state (V) to state or setup time. Also, t_{GTKHDX} symbolizes GMII transmit timing (GT) with respect to the t_{GTX} clock reference (K) going to the high state (H) relative to the time date input signals (D) going invalid (X) or hold time. Note that, in general, the clock reference symbol representation is based on three letters representing the clock of a particular functional. For example, the subscript of t_{GTX} represents the GMII(G) transmit (TX) clock. For rise and fall times, the latter convention is used with the appropriate letter: R (rise) or F (fall).
- This symbol is used to represent the external GTX_CLK125 signal and does not follow the original symbol naming convention.
- In rev. 2.0 silicon, due to errata, t_{GTKHDX} minimum and t_{GTKHDV} maximum are not supported when the GTX_CLK is selected. Refer to Errata *QE_ENET18* in *Chip Errata for the MPC8360E, Rev. 1*.

This figure shows the GMII transmit AC timing diagram.

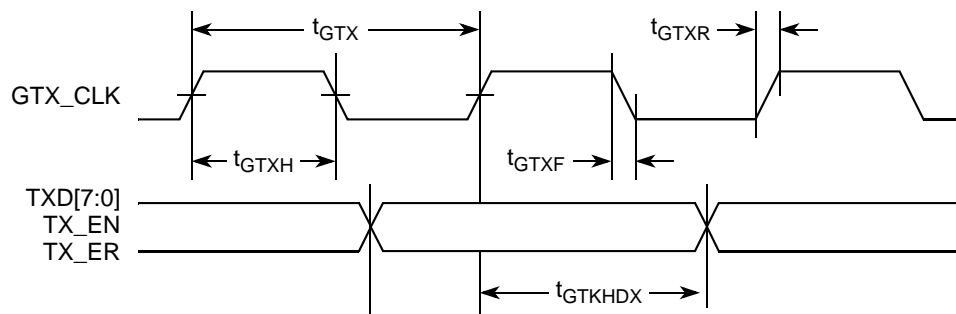


Figure 10. GMII Transmit AC Timing Diagram

8.2.3 RMII AC Timing Specifications

This section describes the RMII transmit and receive AC timing specifications.

8.2.3.1 RMII Transmit AC Timing Specifications

This table provides the RMII transmit AC timing specifications.

Table 31. RMII Transmit AC Timing Specifications

At recommended operating conditions with V_{DD}/OV_{DD} of 3.3 V \pm 10%.

Parameter/Condition	Symbol ¹	Min	Typ	Max	Unit
REF_CLK clock	t_{RMX}	—	20	—	ns
REF_CLK duty cycle	t_{RMXH}/t_{RMX}	35	—	65	%
REF_CLK to RMII data TXD[1:0], TX_EN delay	$t_{RMTKHDX}$ $t_{RMTKHDXV}$	2 —	—	— 10	ns
REF_CLK data clock rise time	t_{RMXR}	1.0	—	4.0	ns
REF_CLK data clock fall time	t_{RMXF}	1.0	—	4.0	ns

Note:

- The symbols used for timing specifications follow the pattern of $t_{(first\ three\ letters\ of\ functional\ block)(signal)(state)(reference)(state)}$ for inputs and $t_{(first\ two\ letters\ of\ functional\ block)(reference)(state)(signal)(state)}$ for outputs. For example, $t_{RMTKHDX}$ symbolizes RMII transmit timing (RMT) for the time t_{RMX} clock reference (K) going high (H) until data outputs (D) are invalid (X). Note that, in general, the clock reference symbol representation is based on two to three letters representing the clock of a particular functional. For example, the subscript of t_{RMX} represents the RMII(RM) reference (X) clock. For rise and fall times, the latter convention is used with the appropriate letter: R (rise) or F (fall).

This figure shows the RMII transmit AC timing diagram.

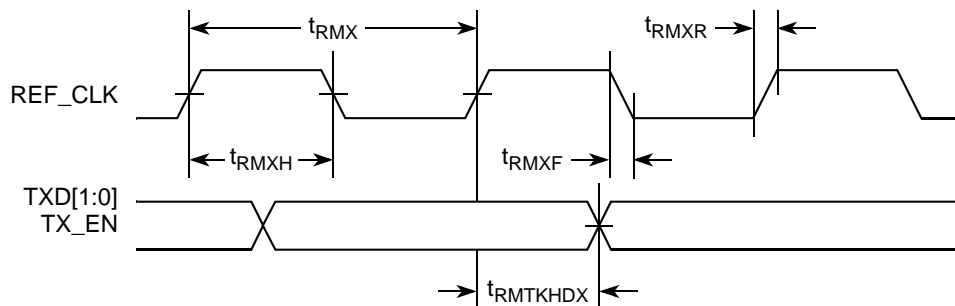


Figure 15. RMII Transmit AC Timing Diagram

8.2.3.2 RMII Receive AC Timing Specifications

This table provides the RMII receive AC timing specifications.

Table 32. RMII Receive AC Timing Specifications

At recommended operating conditions with V_{DD}/OV_{DD} of 3.3 V \pm 10%.

Parameter/Condition	Symbol ¹	Min	Typ	Max	Unit
REF_CLK clock period	t_{RMX}	—	20	—	ns
REF_CLK duty cycle	t_{RMXH}/t_{RMX}	35	—	65	%

Table 40. Local Bus General Timing Parameters—DLL Enabled (continued)

Parameter	Symbol ¹	Min	Max	Unit	Notes
LUPWAIT input hold from local bus clock	$t_{LBIXKH2}$	1.0	—	ns	3, 4
LALE output fall to LAD output transition (LATCH hold time)	$t_{LBOTOT1}$	1.5	—	ns	5
LALE output fall to LAD output transition (LATCH hold time)	$t_{LBOTOT2}$	3.0	—	ns	6
LALE output fall to LAD output transition (LATCH hold time)	$t_{LBOTOT3}$	2.5	—	ns	7
Local bus clock to LALE rise	t_{LBKHLR}	—	4.5	ns	—
Local bus clock to output valid (except LAD/LDP and LALE)	$t_{LBKHOV1}$	—	4.5	ns	—
Local bus clock to data valid for LAD/LDP	$t_{LBKHOV2}$	—	4.5	ns	3
Local bus clock to address valid for LAD	$t_{LBKHOV3}$	—	4.5	ns	3
Output hold from local bus clock (except LAD/LDP and LALE)	$t_{LBKHOX1}$	1.0	—	ns	3
Output hold from local bus clock for LAD/LDP	$t_{LBKHOX2}$	1.0	—	ns	3
Local bus clock to output high impedance for LAD/LDP	t_{LBKHOZ}	—	3.8	ns	8

Notes:

- The symbols used for timing specifications follow the pattern of $t_{(\text{first two letters of functional block})(\text{signal})(\text{state})(\text{reference})(\text{state})}$ for inputs and $t_{(\text{first two letters of functional block})(\text{reference})(\text{state})(\text{signal})(\text{state})}$ for outputs. For example, $t_{LBIXKH1}$ symbolizes local bus timing (LB) for the input (I) to go invalid (X) with respect to the time the t_{LBK} clock reference (K) goes high (H), in this case for clock one (1). Also, t_{LBKHOX} symbolizes local bus timing (LB) for the t_{LBK} clock reference (K) to go high (H), with respect to the output (O) going invalid (X) or output hold time.
- All timings are in reference to rising edge of LSYNC_IN.
- All signals are measured from $OV_{DD}/2$ of the rising edge of LSYNC_IN to $0.4 \times OV_{DD}$ of the signal in question for 3.3-V signaling levels.
- Input timings are measured at the pin.
- $t_{LBOTOT1}$ should be used when RCWH[LALE] is not set and when the load on LALE output pin is at least 10 pF less than the load on LAD output pins.
- $t_{LBOTOT2}$ should be used when RCWH[LALE] is set and when the load on LALE output pin is at least 10 pF less than the load on LAD output pins.
- $t_{LBOTOT3}$ should be used when RCWH[LALE] is set and when the load on LALE output pin equals to the load on LAD output pins.
- For purposes of active/float timing measurements, the Hi-Z or off-state is defined to be when the total current delivered through the component pin is less than or equal to the leakage current specification.

This table describes the general timing parameters of the local bus interface of the device.

Table 41. Local Bus General Timing Parameters—DLL Bypass Mode⁹

Parameter	Symbol ¹	Min	Max	Unit	Notes
Local bus cycle time	t_{LBK}	15	—	ns	2
Input setup to local bus clock	t_{LBIVKH}	7	—	ns	3, 4
Input hold from local bus clock	t_{LBIXKH}	1.0	—	ns	3, 4
LALE output fall to LAD output transition (LATCH hold time)	$t_{LBOTOT1}$	1.5	—	ns	5
LALE output fall to LAD output transition (LATCH hold time)	$t_{LBOTOT2}$	3	—	ns	6
LALE output fall to LAD output transition (LATCH hold time)	$t_{LBOTOT3}$	2.5	—	ns	7

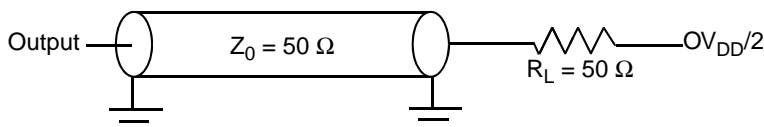
Table 41. Local Bus General Timing Parameters—DLL Bypass Mode⁹ (continued)

Parameter	Symbol ¹	Min	Max	Unit	Notes
Local bus clock to output valid	t_{LBKHOV}	—	3	ns	3
Local bus clock to output high impedance for LAD/LDP	t_{LBKHOZ}	—	4	ns	8

Notes:

1. The symbols used for timing specifications follow the pattern of $t_{(\text{first two letters of functional block})(\text{signal})(\text{state})(\text{reference})(\text{state})}$ for inputs and $t_{(\text{first two letters of functional block})(\text{reference})(\text{state})(\text{signal})(\text{state})}$ for outputs. For example, $t_{LBIXKH1}$ symbolizes local bus timing (LB) for the input (I) to go invalid (X) with respect to the time the t_{LBK} clock reference (K) goes high (H), in this case for clock one (1). Also, t_{LBKHOX} symbolizes local bus timing (LB) for the t_{LBK} clock reference (K) to go high (H), with respect to the output (O) going invalid (X) or output hold time.
2. All timings are in reference to falling edge of LCLK0 (for all outputs and for \overline{LGTA} and LUPWAIT inputs) or rising edge of LCLK0 (for all other inputs).
3. All signals are measured from $OV_{DD}/2$ of the rising/falling edge of LCLK0 to $0.4 \times OV_{DD}$ of the signal in question for 3.3-V signaling levels.
4. Input timings are measured at the pin.
5. $t_{LBOTOT1}$ should be used when RCWH[LALE] is not set and when the load on LALE output pin is at least 10 pF less than the load on LAD output pins.
6. $t_{LBOTOT2}$ should be used when RCWH[LALE] is set and when the load on LALE output pin is at least 10 pF less than the load on LAD output pins.
7. $t_{LBOTOT3}$ should be used when RCWH[LALE] is set and when the load on LALE output pin equals to the load on LAD output pins.
8. For purposes of active/float timing measurements, the Hi-Z or off-state is defined to be when the total current delivered through the component pin is less than or equal to the leakage current specification.
9. DLL bypass mode is not recommended for use at frequencies above 66 MHz.

This figure provides the AC test load for the local bus.


Figure 22. Local Bus C Test Load

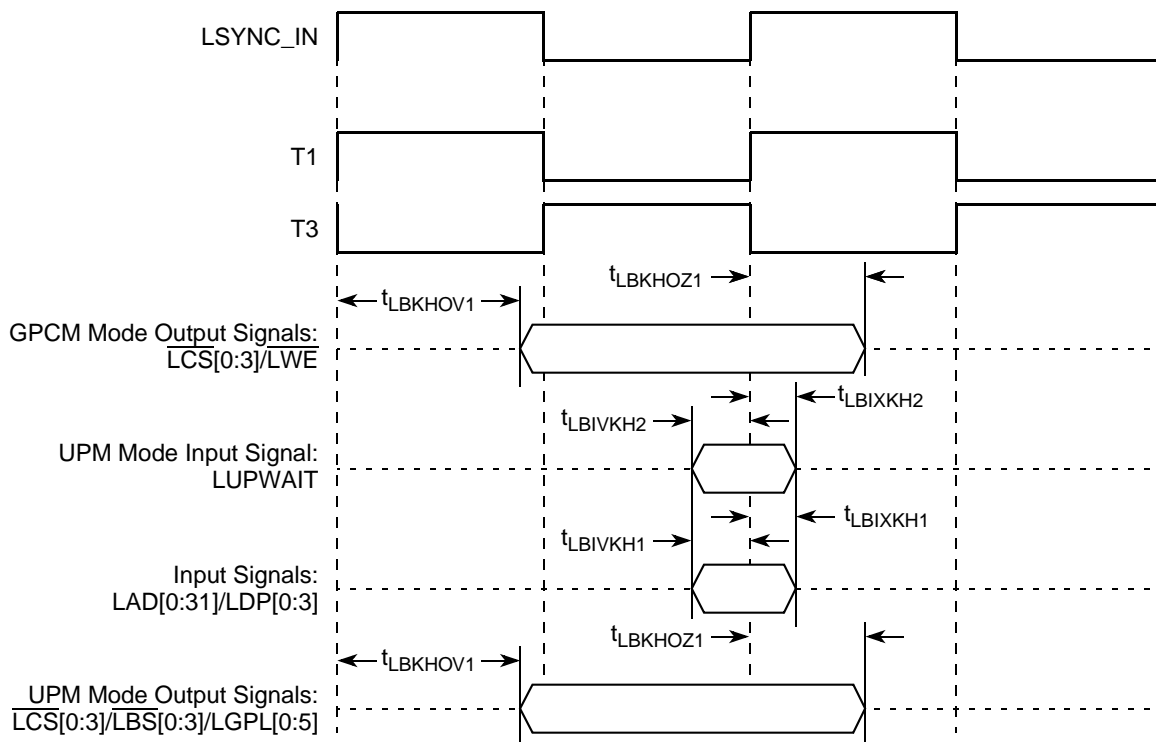


Figure 25. Local Bus Signals, GPCM/UPM Signals for $LCRR[CLKDIV] = 2$ (DLL Enabled)

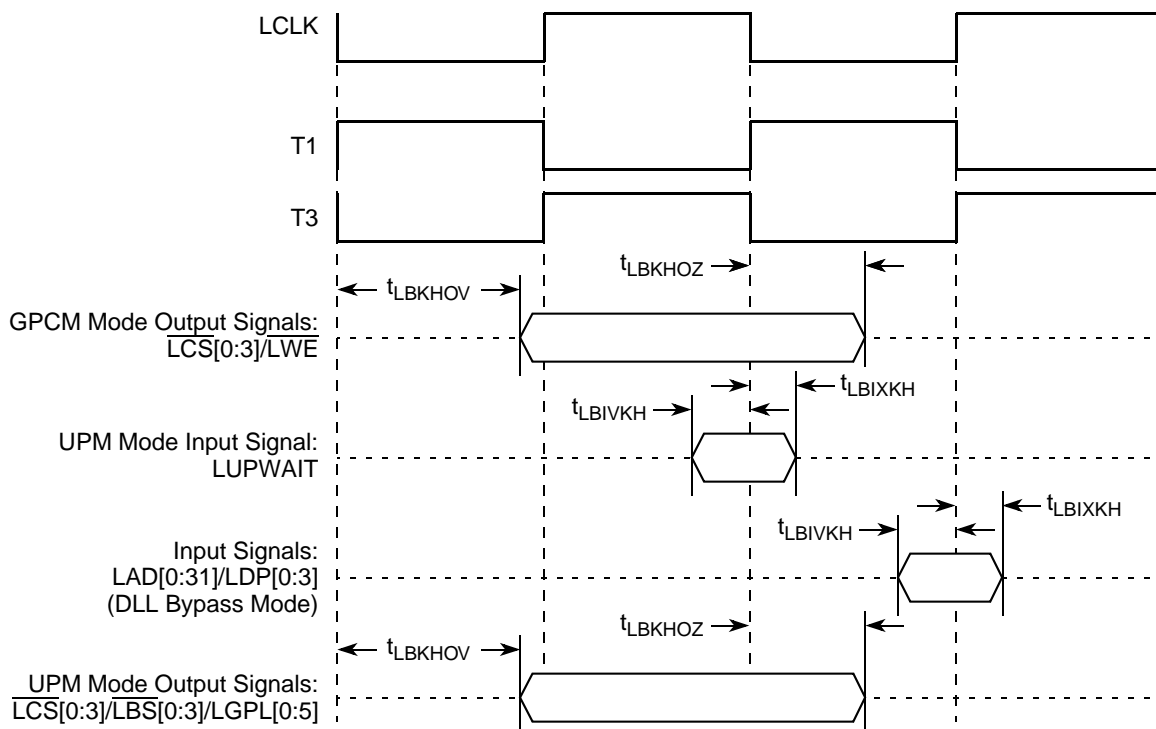


Figure 26. Local Bus Signals, GPCM/UPM Signals for $LCRR[CLKDIV] = 2$ (DLL Bypass Mode)

JTAG AC Electrical Characteristics

This figure provides the AC test load for TDO and the boundary-scan outputs of the device.

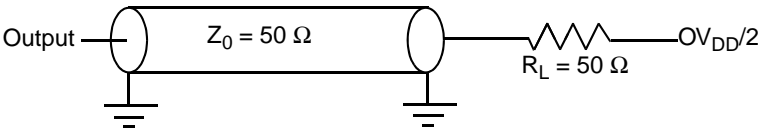


Figure 29. AC Test Load for the JTAG Interface

This figure provides the JTAG clock input timing diagram.

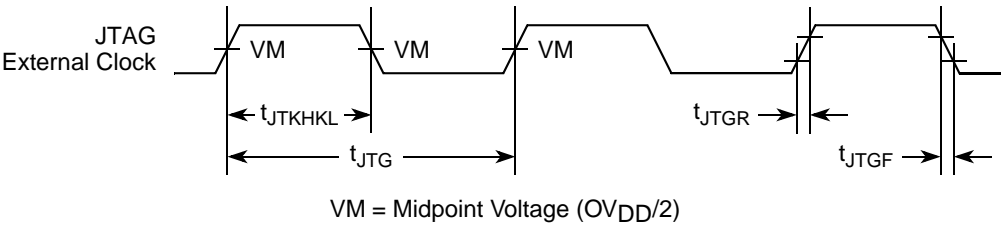


Figure 30. JTAG Clock Input Timing Diagram

This figure provides the \overline{TRST} timing diagram.

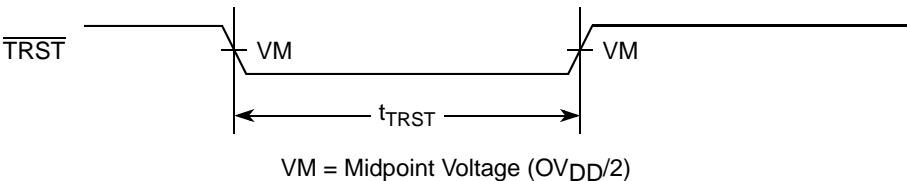


Figure 31. \overline{TRST} Timing Diagram

This figure provides the boundary-scan timing diagram.

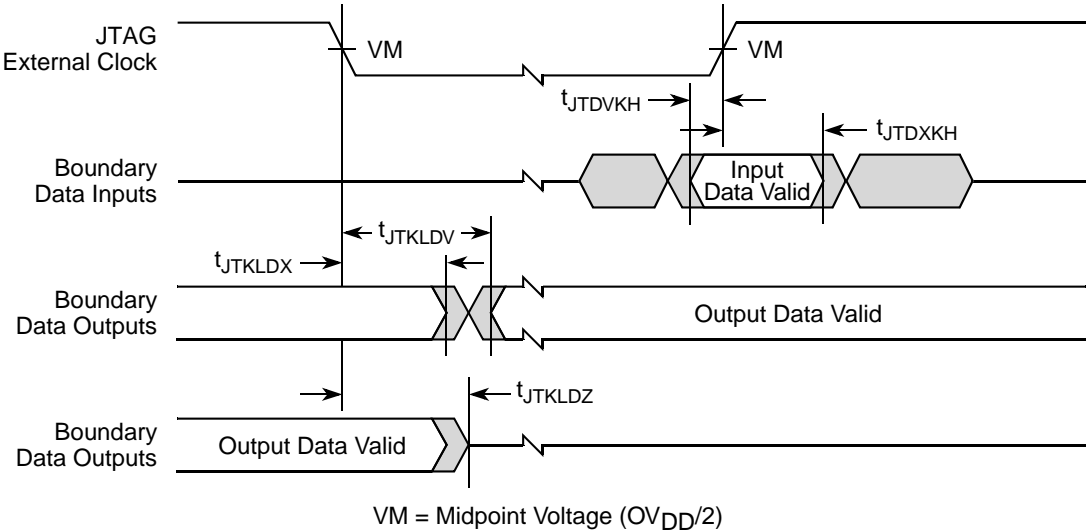


Figure 32. Boundary-Scan Timing Diagram

Table 62. HDLC, BISYNC, and Transparent AC Timing Specifications¹ (continued)

Characteristic	Symbol ²	Min	Max	Unit
Outputs—Internal clock high impedance	t_{HIKHOX}	-0.5	5.5	ns
Outputs—External clock high impedance	t_{HEKHOX}	1	8	ns
Inputs—Internal clock input setup time	t_{HIIVKH}	8.5	—	ns
Inputs—External clock input setup time	t_{HEIVKH}	4	—	ns
Inputs—Internal clock input hold time	t_{HIIXKH}	1.4	—	ns
Inputs—External clock input hold time	t_{HEIXKH}	1	—	ns

Notes:

- Output specifications are measured from the 50% level of the rising edge of CLKIN to the 50% level of the signal. Timings are measured at the pin.
- The symbols used for timing specifications follow the pattern of $t_{(\text{first two letters of functional block})(\text{signal})(\text{state})(\text{reference})(\text{state})}$ for inputs and $t_{(\text{first two letters of functional block})(\text{reference})(\text{state})(\text{signal})(\text{state})}$ for outputs. For example, t_{HIKHOX} symbolizes the outputs internal timing (HI) for the time t_{serial} memory clock reference (K) goes from the high state (H) until outputs (O) are invalid (X).

Table 63. Synchronous UART AC Timing Specifications¹

Characteristic	Symbol ²	Min	Max	Unit
Outputs—Internal clock delay	$t_{UAIKHOV}$	0	11.3	ns
Outputs—External clock delay	$t_{UAEKHOV}$	1	14	ns
Outputs—Internal clock high impedance	$t_{UAIKHOX}$	0	11	ns
Outputs—External clock high impedance	$t_{UAEKHOX}$	1	14	ns
Inputs—Internal clock input setup time	$t_{UAIIVKH}$	6	—	ns
Inputs—External clock input setup time	$t_{UAEIVKH}$	8	—	ns
Inputs—Internal clock input hold time	$t_{UAIIXKH}$	1	—	ns
Inputs—External clock input hold time	$t_{UAEIXKH}$	1	—	ns

Notes:

- Output specifications are measured from the 50% level of the rising edge of CLKIN to the 50% level of the signal. Timings are measured at the pin.
- The symbols used for timing specifications follow the pattern of $t_{(\text{first two letters of functional block})(\text{signal})(\text{state})(\text{reference})(\text{state})}$ for inputs and $t_{(\text{first two letters of functional block})(\text{reference})(\text{state})(\text{signal})(\text{state})}$ for outputs. For example, t_{HIKHOX} symbolizes the outputs internal timing (HI) for the time t_{serial} memory clock reference (K) goes from the high state (H) until outputs (O) are invalid (X).

This figure provides the AC test load.

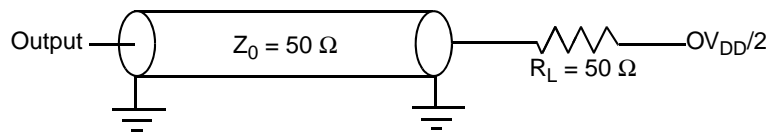


Figure 49. AC Test Load

Table 66. MPC8360E TBGA Pinout Listing (continued)

Signal	Package Pin Number	Pin Type	Power Supply	Notes
LV _{DD0}	D5, D6	Power for UCC1 Ethernet interface (2.5 V, 3.3 V)	LV _{DD0}	—
LV _{DD1}	C17, D16	Power for UCC2 Ethernet interface option 1 (2.5 V, 3.3 V)	LV _{DD1}	9
LV _{DD2}	B18, E21	Power for UCC2 Ethernet interface option 2 (2.5 V, 3.3 V)	LV _{DD2}	9
V _{DD}	C36, D29, D35, E16, F9, F12, F15, F17, F18, F20, F21, F23, F25, F26, F29, F31, F32, F33, G6, J6, K32, M32, N6, P33, R6, R32, U32, V6, Y5, Y32, AB6, AB33, AD6, AF32, AK6, AL6, AM7, AM9, AM10, AM11, AM12, AM13, AM14, AM15, AM18, AM21, AM25, AM28, AM32, AN15, AN21, AN26, AU9, AU17	Power for core (1.2 V)	V _{DD}	—
OV _{DD}	A10, B9, B15, B32, C1, C12, C22, C29, D24, E3, E10, E27, G4, H35, J1, J35, K2, M4, N3, N34, R2, R37, T36, U2, U33, V4, V34, W3, Y35, Y37, AA1, AA36, AB2, AB34	PCI, 10/100 Ethernet, and other standard (3.3 V)	OV _{DD}	—
MVREF1	AN20	I	DDR reference voltage	—
MVREF2	AU32	I	DDR reference voltage	—
SPARE1	B11	I/O	OV _{DD}	8
SPARE3	AH32	—	GV _{DD}	8
SPARE4	AU18	—	GV _{DD}	7
SPARE5	AP1	—	GV _{DD}	8

Table 66. MPC8360E TBGA Pinout Listing (continued)

Signal	Package Pin Number	Pin Type	Power Supply	Notes
No Connect				
NC	AM20, AU19	—	—	—

Notes:

1. This pin is an open drain signal. A weak pull-up resistor (1 k Ω) should be placed on this pin to OV_{DD}.
2. This pin is an open drain signal. A weak pull-up resistor (2–10 k Ω) should be placed on this pin to OV_{DD}.
3. This output is actively driven during reset rather than being three-stated during reset.
4. These JTAG pins have weak internal pull-up P-FETs that are always enabled.
5. This pin should have a weak pull up if the chip is in PCI host mode. Follow PCI specifications recommendation.
6. These are On Die Termination pins, used to control DDR2 memories internal termination resistance.
7. This pin must always be tied to GND.
8. This pin must always be left not connected.
9. Refer to *MPC8360E PowerQUICC II Pro Integrated Communications Processor Reference Manual* section on “RGMII Pins,” for information about the two UCC2 Ethernet interface options.
10. It is recommended that MDIC0 be tied to GND using an 18.2 Ω resistor and MDIC1 be tied to DDR power using an 18.2 Ω resistor for DDR2.

This table shows the pin list of the MPC8358E TBGA package.

Table 67. MPC8358E TBGA Pinout Listing

Signal	Package Pin Number	Pin Type	Power Supply	Notes
DDR SDRAM Memory Controller Interface				
MEMC1_MDQ[0:63]	AJ34, AK33, AL33, AL35, AJ33, AK34, AK32, AM36, AN37, AN35, AR34, AT34, AP37, AP36, AR36, AT35, AP34, AR32, AP32, AM31, AN33, AM34, AM33, AM30, AP31, AM27, AR30, AT32, AN29, AP29, AN27, AR29, AN8, AN7, AM8, AM6, AP9, AN9, AT7, AP7, AU6, AP6, AR4, AR3, AT6, AT5, AR5, AT3, AP4, AM5, AP3, AN3, AN5, AL5, AN4, AM2, AL2, AH5, AK3, AJ2, AJ3, AH4, AK4, AH3	I/O	GV _{DD}	—
MEMC_MECC[0:4]/MSRCID[0:4]	AP24, AN22, AM19, AN19, AM24	I/O	GV _{DD}	—
MEMC_MECC[5]/MDVAL	AM23	I/O	GV _{DD}	—
MEMC_MECC[6:7]	AM22, AN18	I/O	GV _{DD}	—
MEMC_MDM[0:8]	AL36, AN34, AP33, AN28, AT9, AU4, AM3, AJ6, AP27	O	GV _{DD}	—
MEMC_MDQS[0:8]	AK35, AP35, AN31, AM26, AT8, AU3, AL4, AJ5, AP26	I/O	GV _{DD}	—
MEMC_MBA[0:1]	AU29, AU30	O	GV _{DD}	—
MEMC_MBA[2]	AT30	O	GV _{DD}	—
MEMC_MA[0:14]	AU21, AP22, AP21, AT21, AU25, AU26, AT23, AR26, AU24, AR23, AR28, AU23, AR22, AU20, AR18	O	GV _{DD}	—
MEMC_MODT[0:3]	AG33, AJ36, AT1, AK2	O	GV _{DD}	6

ordered, see [Section 24.1, “Part Numbers Fully Addressed by this Document,”](#) for part ordering details and contact your Freescale sales representative or authorized distributor for more information.

Table 69. Operating Frequencies for the TBGA Package

Characteristic ¹	400 MHz	533 MHz	667 MHz ²	Unit
e300 core frequency (<i>core_clk</i>)	266–400	266–533	266–667	MHz
Coherent system bus frequency (<i>csb_clk</i>)	133–333			MHz
QUICC Engine frequency ³ (<i>ce_clk</i>)	266–500			MHz
DDR and DDR2 memory bus frequency (MCLK) ⁴	100–166.67			MHz
Local bus frequency (LCLK _n) ⁵	16.67–133			MHz
PCI input frequency (CLKIN or PCI_CLK)	25–66.67			MHz
Security core maximum internal operating frequency	133	133	166	MHz

Notes:

1. The CLKIN frequency, RCWL[SPMF], and RCWL[COREPLL] settings must be chosen such that the resulting *csb_clk*, MCLK, LCLK[0:2], and *core_clk* frequencies do not exceed their respective maximum or minimum operating frequencies.
2. The 667 MHz core frequency is based on a 1.3 V V_{DD} supply voltage.
3. The 500 MHz QE frequency is based on a 1.3 V V_{DD} supply voltage.
4. The DDR data rate is 2x the DDR memory bus frequency.
5. The local bus frequency is 1/2, 1/4, or 1/8 of the *lb_clk* frequency (depending on LCRR[CLKDIV]) which is in turn 1x or 2x the *csb_clk* frequency (depending on RCWL[LBCM]).

21.1 System PLL Configuration

The system PLL is controlled by the RCWL[SPMF] and RCWL[SVCOD] parameters. This table shows the multiplication factor encodings for the system PLL.

Table 70. System PLL Multiplication Factors

RCWL[SPMF]	System PLL Multiplication Factor
0000	× 16
0001	Reserved
0010	× 2
0011	× 3
0100	× 4
0101	× 5
0110	× 6
0111	× 7
1000	× 8
1001	× 9
1010	× 10
1011	× 11

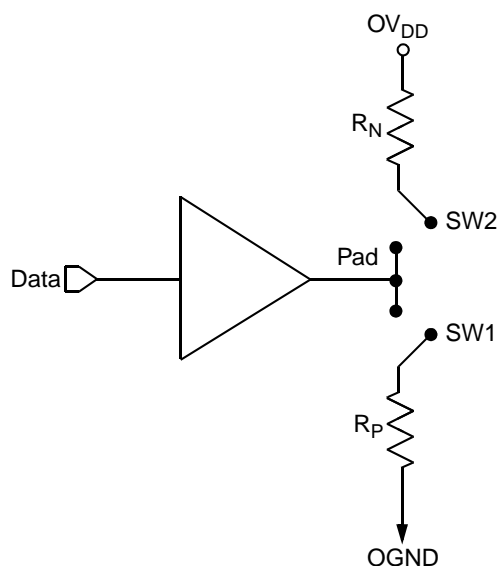


Figure 57. Driver Impedance Measurement

The value of this resistance and the strength of the driver's current source can be found by making two measurements. First, the output voltage is measured while driving logic 1 without an external differential termination resistor. The measured voltage is $V_1 = R_{\text{source}} \times I_{\text{source}}$. Second, the output voltage is measured while driving logic 1 with an external precision differential termination resistor of value R_{term} . The measured voltage is $V_2 = 1/(1/R_1 + 1/R_2) \times I_{\text{source}}$. Solving for the output impedance gives $R_{\text{source}} = R_{\text{term}} \times (V_1/V_2 - 1)$. The drive current is then $I_{\text{source}} = V_1/R_{\text{source}}$.

This table summarizes the signal impedance targets. The driver impedance are targeted at minimum V_{DD} , nominal OV_{DD} , 105°C.

Table 79. Impedance Characteristics

Impedance	Local Bus, Ethernet, DUART, Control, Configuration, Power Management	PCI	DDR DRAM	Symbol	Unit
R_N	42 Target	25 Target	20 Target	Z_0	W
R_P	42 Target	25 Target	20 Target	Z_0	W
Differential	NA	NA	NA	Z_{DIFF}	W

Note: Nominal supply voltages. See Table 1, $T_J = 105^\circ\text{C}$.

23.6 Configuration Pin Muxing

The device provides the user with power-on configuration options that can be set through the use of external pull-up or pull-down resistors of 4.7 kΩ on certain output pins (see customer visible configuration pins). These pins are generally used as output only pins in normal operation.

While $\overline{\text{HRESET}}$ is asserted however, these pins are treated as inputs. The value presented on these pins while $\overline{\text{HRESET}}$ is asserted, is latched when $\overline{\text{HRESET}}$ deasserts, at which time the input receiver is disabled and the I/O circuit takes on its normal function. Careful board layout with stubless connections to these pull-up/pull-down resistors coupled with the large value of the pull-up/pull-down resistor should minimize the disruption of signal quality or speed for output pins thus configured.

23.7 Pull-Up Resistor Requirements

The device requires high resistance pull-up resistors (10 k Ω is recommended) on open drain type pins including I²C pins, Ethernet Management MDIO pin, and EPIC interrupt pins.

For more information on required pull-up resistors and the connections required for the JTAG interface, see *MPC8360E/MPC8358E PowerQUICC Design Checklist* (AN3097).

24 Ordering Information

24.1 Part Numbers Fully Addressed by this Document

This table provides the Freescale part numbering nomenclature for the MPC8360E/58E. Note that the individual part numbers correspond to a maximum processor core frequency. For available frequencies, contact your local Freescale sales office. Additionally to the processor frequency, the part numbering scheme also includes an application modifier, which may specify special application conditions. Each part number also contains a revision code that refers to the die mask revision number.

Table 80. Part Numbering Nomenclature¹

<i>MPC</i>	<i>nnnn</i>	<i>e</i>	<i>t</i>	<i>pp</i>	<i>aa</i>	<i>a</i>	<i>a</i>	<i>A</i>
Product Code	Part Identifier	Encryption Acceleration	Temperature Range	Package ²	Processor Frequency ³	Platform Frequency	QUICC Engine Frequency	Die Revision
MPC	8358	Blank = not included E = included	Blank = 0° C T _A to 105° C T _J C = -40° C T _A to 105° C T _J	ZU = TBGA VV = TBGA (no lead)	e300 core speed AD = 266 MHz AG = 400 MHz	D = 266 MHz	E = 300 MHz G = 400 MHz	A = rev. 2.1 silicon
	8360				e300 core speed AG = 400 MHz AJ = 533 MHz AL = 667 MHz	D = 266 MHz F = 333 MHz	G = 400 MHz H = 500 MHz	A = rev. 2.1 silicon
MPC (rev. 2.0 silicon only)	8360	Blank = not included E = included	0° C T _A to 70° C T _J	ZU = TBGA VV = TBGA (no lead)	e300 core speed AH = 500 MHz AL = 667 MHz	F = 333 MHz	G = 400 MHz H = 500 MHz	—

Notes:

1. Not all processor, platform, and QUICC Engine block frequency combinations are supported. For available frequency combinations, contact your local Freescale sales office or authorized distributor.
2. See [Section 20, "Package and Pin Listings,"](#) for more information on available package types.
3. Processor core frequencies supported by parts addressed by this specification only. Not all parts described in this specification support all core frequencies. Additionally, parts addressed by part number specifications may support other maximum core frequencies.

This table shows the SVR settings by device and package type.

Table 81. SVR Settings

Device	Package	SVR (Rev. 2.0)	SVR (Rev. 2.1)
MPC8360E	TBGA	0x8048_0020	0x8048_0021
MPC8360	TBGA	0x8049_0020	0x8049_0021

Table 82. Revision History (continued)

Rev. Number	Date	Substantive Change(s)
3	03/2010	<ul style="list-style-type: none"> • Changed references to RCWH[PCICKEN] to RCWH[PCICKDRV]. • In Table 2, added extended temperature characteristics. • Added Figure 6, “DDR Input Timing Diagram.” • In Figure 53, “Mechanical Dimensions and Bottom Surface Nomenclature of the TBGA Package,” removed watermark. • Updated the title of Table 19, “DDR SDRAM Input AC Timing Specifications.” • In Table 20, “DDR and DDR2 SDRAM Input AC Timing Specifications Mode,” changed table subtitle. • In Table 27–Table 30, and Table 33–Table 34, changed the rise and fall time specifications to reference 20–80% and 80–20% of the voltage supply, respectively. • In Table 38, “IEEE 1588 Timer AC Specifications,” changed first parameter to “Timer clock frequency.” • In Table 45, “I2C AC Electrical Specifications,” changed units to “ns” for t_{I2DVKH}. • In Table 66, “MPC8360E TBGA Pinout Listing,” and Table 67 “MPC8358E TBGA Pinout Listing,” added note 7: “This pin must always be tied to GND” to the TEST pin and added a note to SPARE1 stating: “This pin must always be left not connected.” • In Section 4, “Clock Input Timing,” added note regarding rise/fall time on QUICC Engine block input pins. • Added Section 4.3, “Gigabit Reference Clock Input Timing.” • Updated Section 8.1.1, “10/100/1000 Ethernet DC Electrical Characteristics.” • In Section 20.3, “Pinout Listings,” added sentence stating “Refer to AN3097, ‘MPC8360/MPC8358E PowerQUICC Design Checklist,’ for proper pin termination and usage.” • In Section 21, “Clocking,” removed statement: “The OCCR[PCICDn] parameters select whether CLKIN or CLKIN/2 is driven out on the PCI_CLK_OUTn signals.” • In Section 21.1, “System PLL Configuration,” updated the system VCO frequency conditions. • In Table 80, added extended temperature characteristics.
2	12/2007	Initial release.